

NPN 2N3054

SILICON POWER TRANSISTORS

The 2N3054 are NPN transistors mounted in TO-66 metal package with the collector connected to the case .

They Designed for general purpose switching and amplifier applications. Compliance to RoHS.

ABSOLUTE MAXIMUM RATINGS

Symbol	Ratings		Value	Unit	
V _{CEO}	Collector-Emitter Voltage (I _B = 0)		55	V	
V _{CBO}	Collector-Base Voltage (I _E = 0)		90	V	
V _{EBO}	Emitter-Base Voltage (I _C = 0)		7	V	
Ic	Collector Current		4	А	
I _{CM}	Peak Collector Current		10		
I _B	Base Current		2	Α	
P _D	Total Power Dissipation @ T _{case} = 25°		25	W	
TJ	Junction Temperature		200	°C	
T _{Stg}	Storage Temperature range		-65 to +200	°C	

THERMAL CHARACTERISTICS

Symbol	Ratings	Value	Unit
R _{thJ-c}	Thermal Resistance, Junction-case	7	°C/W

ELECTRICAL CHARACTERISTICS

TC=25°C unless otherwise noted

Symbol	Ratings	Test Condition(s)	Min	Тур	Max	Unit
I _{CEO}	Collector Cut-Off Current	$V_{CE} = 30 \text{ V}, I_{B} = 0$	-	-	0.5	
I _{EBO}	Emitter Cut-Off Current	$V_{EB} = 7V, I_{C} = 0$	-	-	1	mA
I _{CEV}	Collector Cut-Off Current	$V_{CE} = 90V$ $T_{C} = 25^{\circ}C$	-	-	1	IIIA
	Collector Cut-Oil Current	$V_{BE} = 1.5V$ $T_{C} = 150^{\circ}C$	C -	-	6	
V _{CEO} (*)	Collector Emitter Breakdown Voltage	I _C =0.1 mA, I _B =0	55	-	-	٧
h _{FE} (*)	DC Current Gain	I_{C} = 100 mA, V_{CE} = 10 V	40	-	-	
		I _C = 1 A, V _{CE} = 2 V	8	-	80	-
V _{CE(SAT)} (*)	Collector-Emitter saturation	I_{C} = 500 mA, I_{B} = 50 mA	-	-	1	V
	Voltage	$I_{C}=3 A, I_{B}=1 A$	-	-	6	V
V_{BE}	Base-Emitter Voltage	I_{C} = 500 mA, V_{CE} = 4 V	-	-	1.7	V
f _T	Transition Frequency	I _C = 200 mA, V _{CE} =10 V f= 1 MHz	500	-	-	MHz

^(*) Pulse conditions : tp < 300 μ s, δ =2%.

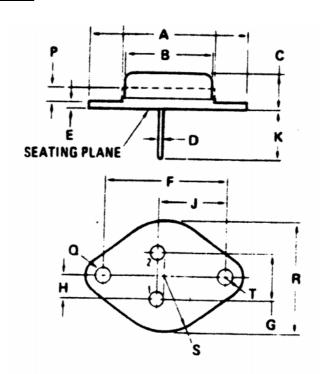


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MECHANICAL DATA CASE TO-66

DIMENSIONS			
	mm		
	min	max	
Α	30.60	32.52	
В	11.94	12.7	
B C D E	6.35	8.63	
D	0.712	0.863	
	1.27	1.91	
F	24.28	24.50	
G	4.83	5.33	
Н	2.41	2.67	
J	14.48	14.99	
K	9.15	10.50	
Р	-	2.7	
Q S	3.60	4.00	
S	-	8.89	
Т	-	3.68	

Pin 1 :	Emitter
Pin 2 :	Base
Case:	Collector



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